



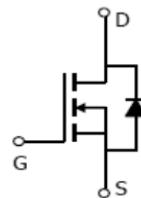
Product Summary

This device is suitable for use as a load switch or in PWM applications.

R_{DS(ON)} to minimize conductive loss
fast switching

PWM

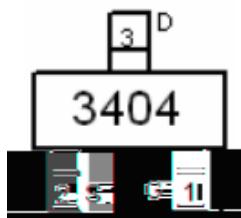
nd Synchronous Rectifier



V_{DS} = 30V

R_{DS(ON)} = 19m

I_D = 5A



SOT-23

Part NO.	ZM3404
Marking	3404
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

Absolute Maximum Ratings T_c = 25

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	20	V
Continuous Drain Current	I _D @T _C =25	5	A
	I _D @T _C =75	3.8	A
	I _D @T _C =100	3.1	A
Pulsed Drain Current	I _{DM}	30	A
Total Power Dissipation(TA=25)	P _D @TA=25	1.3	W
Total Power Dissipation(TA=25)	P _D @TA=70	0.9	W
Operating Junction Temperature	T _J	-55 to 150	
Storage Temperature	T _{STG}	-55 to 150	



Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	1.2	1.8	2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 30V, V_{GS} = 0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 4.5A$.3	
		$V_{GS} = 4.5V, I_D = 4A$.4	0	
Forward Transconductance	g_{FS}	$V_{DS} = 5V, I_D = 5A$		1		
Source-Drain Voltage	V_{SD}	$V_{GS} = 0V S = 1A$				

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	$V_{GS} = 0V$	-	390	-	
Output capacitance	C_{oss}	$V_{DS} = 15V$ $f = 1MHz$				pF



Fig.1 Power Dissipation

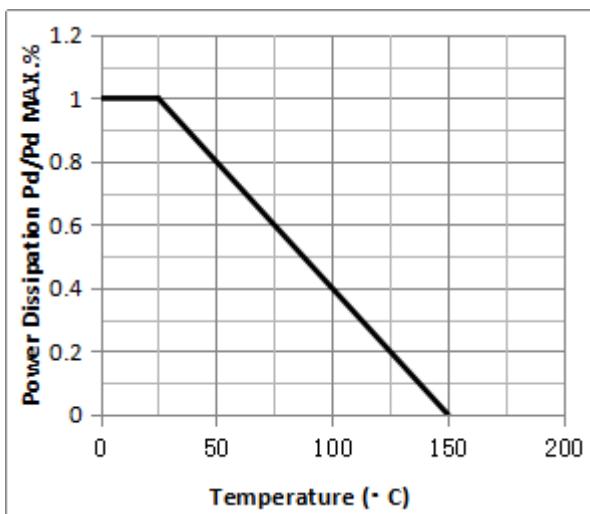


Fig.2 Typical output Characteristics

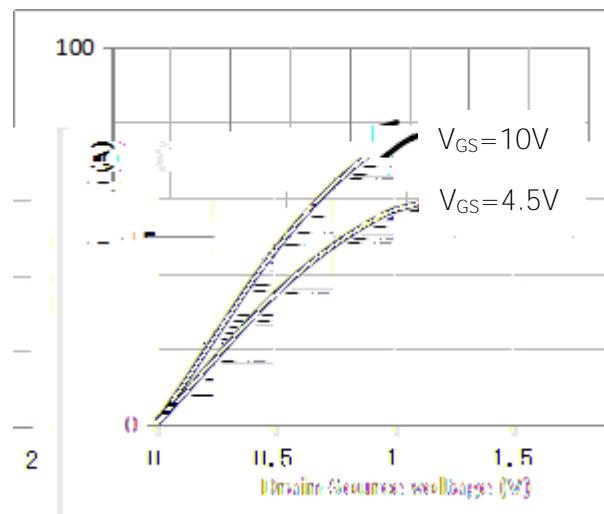


Fig.3 Threshold Voltage V.S Junction Temperature

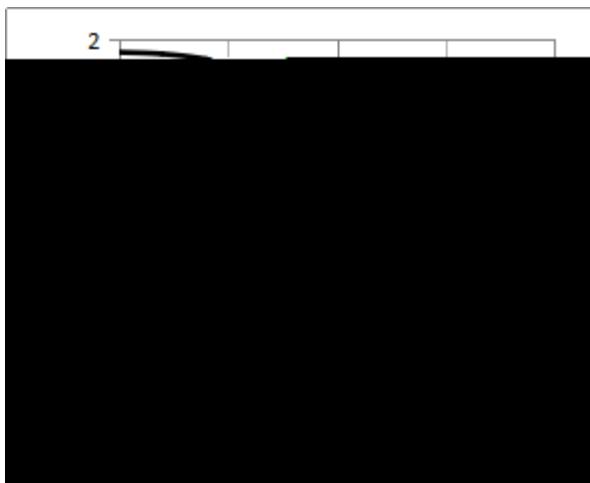


Fig.4 Resistance V.S Drain Current

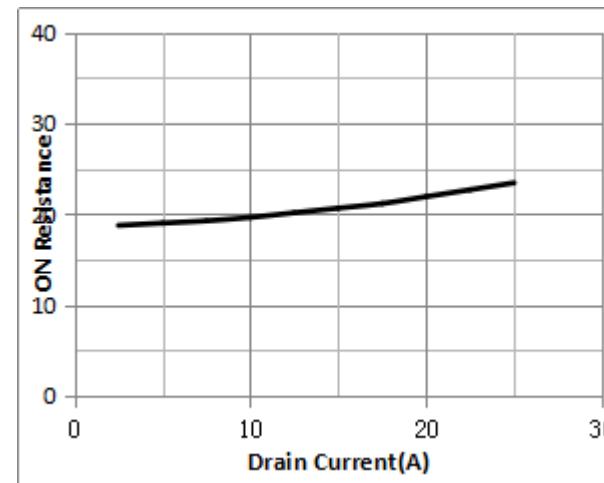


Fig.5 On-Resistance VS Gate Source Voltage

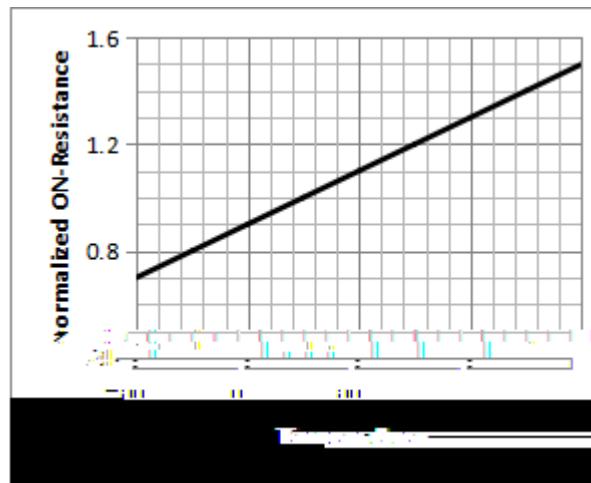
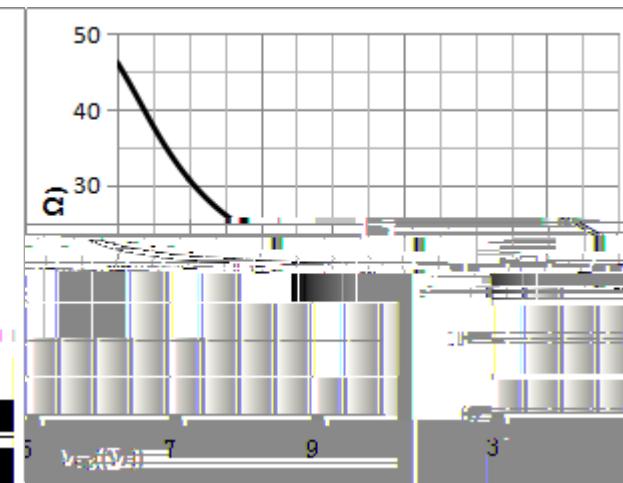


Fig.6 On-Resistance V.S Junction Temperature







ZMJ SEMICONDUCTOR CO., LTD

ZM3404
30V N-CHANNEL MOSFET

Dimensions (SOT-23)

Unit mm

